



2.5-V/3.3-V OSCILLATOR GAIN STAGE/BUFFERS

FEATURES

- Low-Voltage PECL Input and Low-Voltage **PECL or LVDS Outputs**
- Clock Rates to 2 GHz
 - 140-ps Output Transition Times
 - 0.11 ps Typical Intrinsic Phase Jitter
 - Less than 630 ps Propagation Delay Times
- 2.5-V or 3.3-V Supply Operation

2-mm × 2-mm Small-Outline **No-Lead Package**

APPLICATIONS

- **PECL-to-LVDS Translation**
- **Clock Signal Amplification**

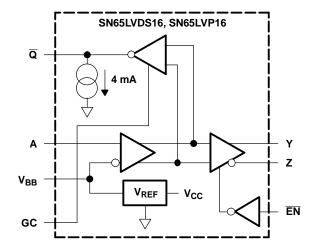
DESCRIPTION

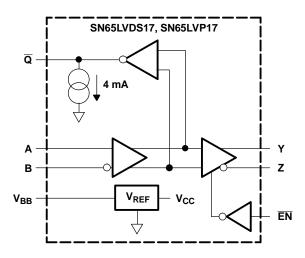
These four devices are high-frequency oscillator gain stages supporting both LVPECL or LVDS on the high gain outputs in 3.3-V or 2.5-V systems. Additionally, provides the option of both single-ended input (PECL levels on the SN65LVx16) and fully differential inputs on the SN65LVx17.

The SN65LVx16 provides the user a Gain Control (GC) for controlling the Q output from 300 mV to 860 mV either by leaving it open (NC), grounded, or tied to V_{CC} . (When left open, the \overline{Q} output defaults to 575 mV.) The Q on the SN65LVx17 defaults to 575 mV as well.

Both devices provide a voltage reference (V_{BB}) of typically 1.35 V below V_{CC} for use in receiving single-ended PECL input signals. When not used, V_{BB} should be unconnected or open.

All devices are characterized for operation from -40°C to 85°C.







Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS(1)

INPUT	OUTPUT	GAIN CONTROL	BASE PART NUMBER	PART MARKING
Single-ended	LVDS	Yes	SN65LVDS16	EL
Single-ended	LVPECL	Yes	SN65LVP16	EK
Differential	LVDS	No	SN65LVDS17	EN
Differential	LVPECL	No	SN65LVP17	EM

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

		UNIT
V_{CC}	Supply voltage ⁽²⁾	–0.5 V to 4 V
V_{I}	Input voltage	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Vo	Output voltage	-0.5 V to V _{CC} + 0.5 V
Io	V _{BB} output current	±0.5 mA
	HBM electrostatic discharge ⁽³⁾	±3 kV
	CDM electrostatic discharge (4)	±1500 V
	Continuous power dissipation	See Power Dissipation Ratings Table

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS

PACKAGE	CIRCUIT BOARD MODEL A		DERATING FACTOR ABOVE $T_A = 25^{\circ}C^{(1)}$	T _A = 85°C POWER RATING
DRF	Low-K ⁽²⁾	403 mW	4.0 mW/°C	161 mW
DKF	High-K ⁽³⁾	834 mW	8.3 mW/°C	333 mW

⁽¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	VALUE	UNIT	
θ_{JB}	Junction-to-board thermal resistance	•		93.3	°C/W	
θ _{JC} Junction-to-case thermal resistance			101.7	C/VV		
		Typical		V _{CC} = 3.3 V, T _A = 25°C, 2 GHz, LVDS	132	
Ь	Device newer dissination	Typical	V _{CC} = 3.3 V, T _A = 25°C, 2 GHz, LVPECL	83	mW	
PD	P _D Device power dissipation	Maximum	V _{CC} = 3.6 V, T _A = 85°C, 2 GHz, LVDS	173	IIIVV	
		Maximum	V _{CC} = 3.6 V, T _A = 85°C, 2 GHz, LVPECL	108		

⁽²⁾ All voltage values, except differential voltages, are with respect to network ground see Figure 1).

³⁾ Tested in accordance with JEDEC Standard 22, Test Method A114-A-7

⁽⁴⁾ Tested in accordance with JEDEC Standard 22, Test Method C101

⁽²⁾ In accordance with the Low-K thermal metric definitions of EIA/JESD51-3.

⁽³⁾ In accordance with the High-K thermal metric definitions of EIA/JESD51-7.



RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.375	2.5 or 3.3	3.6	V
V_{IC}	Common-mode input voltage (V _{IA} + V _{IB})/2	SN65LVDS17 or SN65LVP17	1.2		$V_{CC}-\left(V_{ID}/2\right)$	٧
$ V_{ID} $	Differential input voltage magnitude $ V_{IA} - V_{IB} $	SN65LVDS17 or SN65LVP17	0.08		1	٧
\/	High level input valtage to EN	EN	2		V_{CC}	٧
V _{IH}	High-level input voltage to EN	SN65LVDS16 or SN65LVP16	V _{CC} - 1.17		V _{CC} - 0.44	V
\/	Low-level input voltage to EN	EN	0		0.8	V
V _{IL}	Low-level input voltage to EN	SN65LVDS16 or SN65LVP16	V _{CC} - 2.25		V _{CC} - 1.52	V
Io	Output current to V _{BB}		-400 ⁽¹⁾		400	μA
R_{L}	Differential load resistance,		90		132	Ω
T_A	Operating free-air temperature	-40		85	°C	

⁽¹⁾ The algebraic convention, where the least positive (more negative) value is designated minimum, is used in this data sheet.

ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
	Cumply overent	$R_L = 100 \ \Omega, \ \overline{EN} \ \text{at 0 V},$ Other inputs open		40	48	mA
Icc	Supply current	Outputs unloaded, EN at 0 V, Other inputs open		25	30	MA
V_{BB}	Reference voltage (2)	$I_{BB} = -400 \mu A$	V _{CC} - 1.44	V _{CC} - 1.35	V _{CC} - 1.25	V
I _{IH}	High-level input current, EN	$V_I = 2 V$	-20		20	
I _{IAH} or I _{IBH}	High-level input current, A or B	$V_I = V_{CC}$	-20		20	
I _{IL}	Low-level input current, EN	V _I = 0.8 V	-20		20	μΑ
I _{IAL} or I _{IBL}	Low-level input current, A or B	V _I = GND	-20		20	
SN65LVDS1	6/17 Y AND Z OUTPUT CHARACTERI	STICS				
V _{OD}	Differential output voltage magnitude, $ V_{OY} - V_{OZ} $		247	340	454	mV
$\Delta V_{OD} $	Change in differential output voltage magnitude between logic states	See Figure 1 and Figure 2			50	IIIV
V _{OC(SS)}	Steady-state common-mode output voltage (see Figure 3)		1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common- mode output voltage between logic states	See Figure 3	-50		50	mV
V _{OC(PP)}	Peak-to-peak common-mode output voltage			50	100	
I _{OYZ} or I _{OZZ}	High-impedance output current	$\overline{\text{EN}}$ at V_{CC} , $V_{\text{O}} = 0 \text{ V or } V_{\text{CC}}$	-1		1	μΑ
I _{OYS} or I _{OZS}	Short-circuit output current	$\overline{\text{EN}}$ at 0 V, V_{OY} or $V_{\text{OZ}} = 0 \text{ V}$	-62		62	
I _{OS(D)}	Differential short-circuit output current, I _{OY} - I _{OZ}	$\overline{\text{EN}}$ at 0 V, $V_{OY} = V_{OZ}$	-12		12	mA

 $[\]begin{array}{ll} \hbox{(1)} & \hbox{Typical values are at room temperature and with a V_{CC} of 3.3 V.} \\ \hbox{(2)} & \hbox{Single-ended input operation is limited to $V_{CC}$$\ge 3.0 V.} \\ \end{array}$



ELECTRICAL CHARACTERISTICS (continued)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
SN65LVP16	/17 Y AND Z OUTPUT CHARACTERIS	TICS				
V _{OYH} or V _{OZH}	High-level output voltage	3.3 V; 50 Ω from Y and Z	V _{CC} - 1.05		V _{CC} - 0.82	
V _{OYL} or V _{OZL}	Low-level output voltage	to V _{CC} - 2 V	V _{CC} - 1.83		V _{CC} - 1.57	V
V _{OYL} or V _{OZL}	Low-level output voltage	2.5 V; 50 Ω from Y and Z to V _{CC} – 2 V	V _{CC} - 1.88		V _{CC} - 1.57	V
V _{OD}	Differential output voltage magnitude, $ V_{OH} - V_{OL} $		0.6	0.8 1		
I _{OYZ} or I _{OZZ}	High-impedance output current	$\overline{\text{EN}}$ at V_{CC} , $V_{\text{O}} = 0 \text{ V or } V_{\text{CC}}$	-1		1	μΑ
Q OUTPUT	CHARACTERISTICS (see Figure 1)					
V_{OH}	High-level output voltage	No load		V _{CC} - 0.94		V
		GC Tied to GND, No load		V _{CC} - 1.22		
V_{OL}	Low-level output voltage	GC Open, No load		V _{CC} - 1.52 V _{CC} - 1.82		V
		GC Tied to V _{CC} , No load				
		GC Tied to GND		300		
$V_{O(pp)}$	Peak-to-peak output voltage	GC Open		575		mV
		GC Tied to V _{CC}		860		

SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

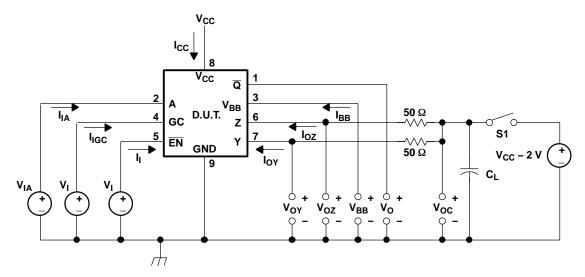
	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
	Decreasion delegations to ant	A to Q			340	460	
t _{PD}	Propagation delay time, t _{PLH} or t _{PHL}	D to Y or Z	See Figure 4		460	630	ps
t _{SK(P)}	Pulse skew, t _{PLH} - t _{PHL}					20	
	t _{SK(PP)} Part-to-part skew ⁽²⁾		V _{CC} = 3.3 V			80	20
t _{SK(PP)}	rait-to-part skew (=)		V _{CC} = 2.5 V			130	ps
t _r	20%-to-80% differential signal rise tin	me	See Figure 4		85	140	ps
t _f	20%-to-80% differential signal fall tin	ne	See Figure 4		85	140	ps
t _{jit(per)}	RMS period jitter ⁽³⁾		2-GHz 50%-duty-cycle square-wave input,		2	3	20
t _{jit(cc)}	Peak cycle-to-cycle jitter ⁽⁴⁾		See Figure 5		15	23	ps B
t _{jit(ph)}	Intrinsic phase jitter		2 GHz		0.11		ps
t _{PHZ}	Propagation delay time, high-level-to-high-impedance output					30	
t _{PLZ}	Propagation delay time, low-level-to-high-impedance output		Con Figure 6			30	
t _{PZH}	Propagation delay time, high-impedance-to-high-level output		See Figure 6			30	ns
t _{PZL}	Propagation delay time, high-impedance-to-low-level output					30	

Typical values are at room temperature and with a V_{CC} of 3.3 V. Part-to-part skew is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

Period jitter is the deviation in cycle time of a signal with respect to the ideal period over a random sample of 100,000 cycles. Cycle-to-cycle jitter is the variation in cycle time of a signal between adjacent cycles, over a random sample of 1,000 adjacent cycle

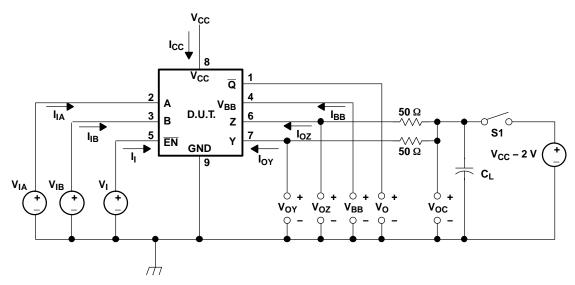


PARAMETER MEASUREMENT INFORMATION



- (1) C_L is the instrumentation and test fixture capacitance.
- (2) S1 is open for the SN65LVDS16 and closed for the SN65LVP16.

Figure 1. Output Voltage Test Circuit and Voltage and Current Definitions for LVDS/LVP16



- (1) C_L is the instrumentation and test fixture capacitance.
- (2) S1 is open for the SN65LVDS17 and closed for the SN65LVP17.

Figure 2. Output Voltage Test Circuit and Voltage and Current Definitions for LVDS/LVP17

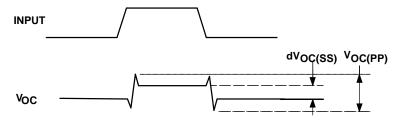


Figure 3. V_{oc} Definitions



PARAMETER MEASUREMENT INFORMATION (continued)

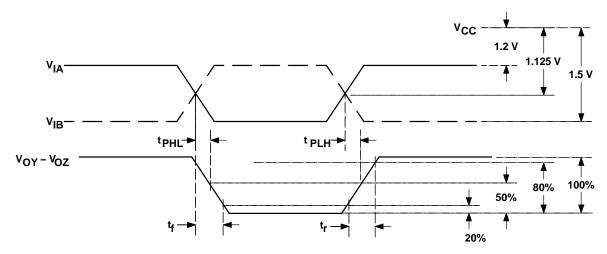


Figure 4. Propagation Delay and Transition Time Test Waveforms

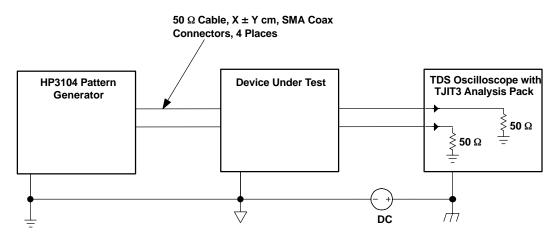


Figure 5. Jitter Measurement Setup



PARAMETER MEASUREMENT INFORMATION (continued)

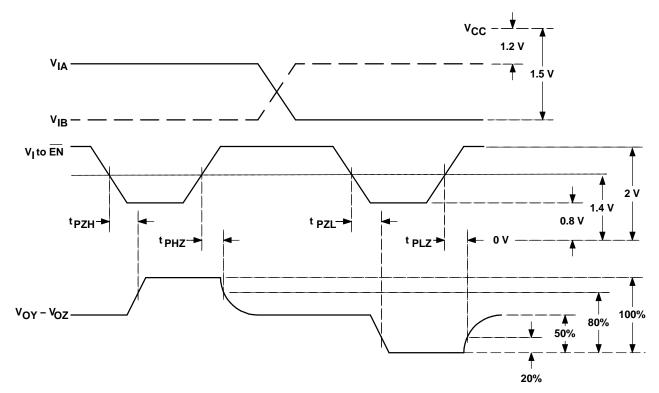


Figure 6. Enable and Disable Time Test Waveforms



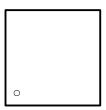
DEVICE INFORMATION

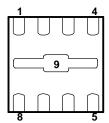
FUNCTION TABLE

	SN65LV	DS16, SN65	LVP16 ⁽¹⁾			SN65LVDS17, SN65LVP17 ⁽¹⁾				
Α	EN	Q	Y	Z	Α	В	EN	Q	Y	Z
Н	L	L	Н	L	Н	Н	L	?	?	?
L	L	Н	L	Н	L	Н	L	Н	L	Н
Χ	Н	?	Z	Z	Н	L	L	L	Н	L
Open	L	?	?	?	L	L	L	?	?	?
Χ	Open	?	?	?	Х	X	Н	?	Z	Z
					Open	Open	L	?	?	?
					Х	Х	Open	?	?	?

(1) H = high, L = low, Z = high impedance, ? = indeterminate

DRF PACKAGE TOP VIEW





BOTTOM VIEW

Package Pin Assignments - Numerical Listing

SN65LVDS1	6, SN65LVP16	SN65LVDS17	, SN65LVP17	
PIN	SIGNAL	PIN	SIGNAL	
1	Q	1	Q	
2	А	2	A	
3	V_{BB}	3	В	
4	GC	4	V _{BB}	
5	EN	5	EN	
6	Z	6	Z	
7	Y	7	Y	
8	V _{CC}	8	V _{CC}	
9	GND	9	GND	



TYPICAL CHARACTERISTICS

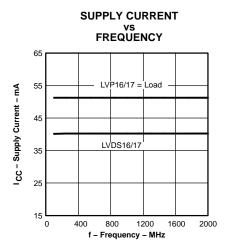


Figure 7.

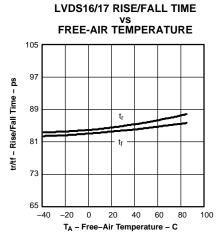


Figure 9.

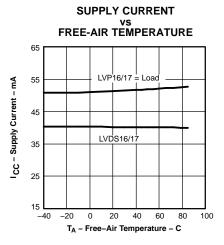


Figure 8.

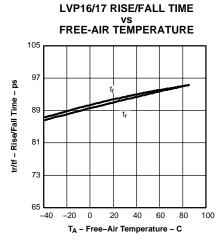
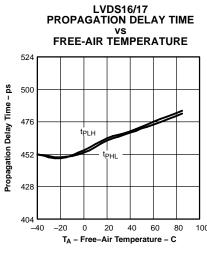


Figure 10.





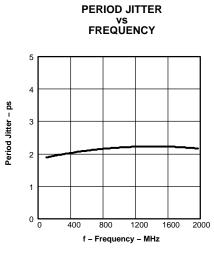
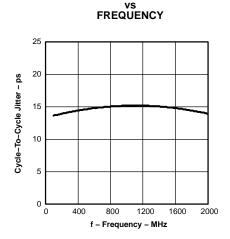


Figure 12.



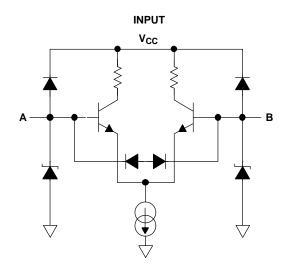
CYCLE-TO-CYCLE JITTER

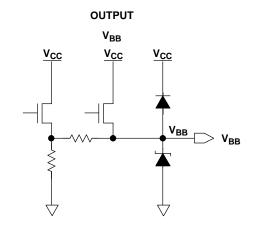
Figure 13.



EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

OUTPUT LVP16/17 OUTPUT LVDS16/17 ν_{cc} v_{cc} v_{cc} v_{cc} v_{cc} R R V_{CC} **⊸ z** Y 0-7 V v_{cc} **ENABLE** 400 Ω 300 $\mathbf{k}\Omega$





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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65LVDS16DRFT	ACTIVE	WSON	DRF	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EL	Samples
SN65LVDS17DRFR	ACTIVE	WSON	DRF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EN	Samples
SN65LVDS17DRFT	ACTIVE	WSON	DRF	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EN	Samples
SN65LVP16DRFT	ACTIVE	WSON	DRF	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EK	Samples
SN65LVP17DRFT	ACTIVE	WSON	DRF	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	EM	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

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Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS16DRFT	WSON	DRF	8	250	330.0	8.8	2.3	2.3	1.0	4.0	8.0	Q2
SN65LVDS17DRFR	WSON	DRF	8	3000	330.0	8.8	2.3	2.3	1.0	4.0	8.0	Q2
SN65LVDS17DRFT	WSON	DRF	8	250	330.0	8.8	2.3	2.3	1.0	4.0	8.0	Q2
SN65LVP16DRFT	WSON	DRF	8	250	330.0	8.8	2.3	2.3	1.0	4.0	8.0	Q2
SN65LVP17DRFT	WSON	DRF	8	250	330.0	8.8	2.3	2.3	1.0	4.0	8.0	Q2

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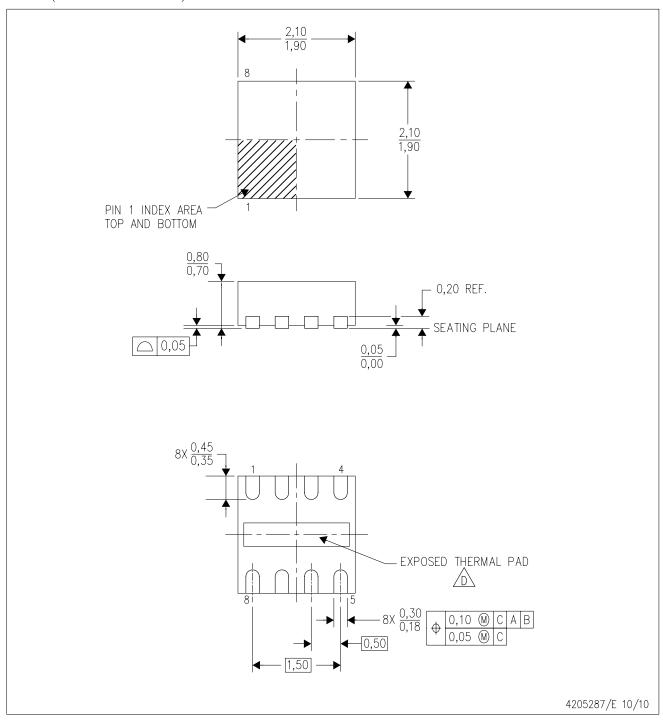


*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS16DRFT	WSON	DRF	8	250	337.0	343.0	29.0
SN65LVDS17DRFR	WSON	DRF	8	3000	337.0	343.0	29.0
SN65LVDS17DRFT	WSON	DRF	8	250	337.0	343.0	29.0
SN65LVP16DRFT	WSON	DRF	8	250	337.0	343.0	29.0
SN65LVP17DRFT	WSON	DRF	8	250	337.0	343.0	29.0

DRF (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- Ç. Quad Flatpack, No-Leads (QFN) package configuration.
- The Package thermal pad must be soldered to the board for thermal and mechanical performance. See product data sheet for details regarding the exposed thermal pad dimensions.
- E. Falls within JEDEC MO-229.



DRF (S-PWSON-N8)

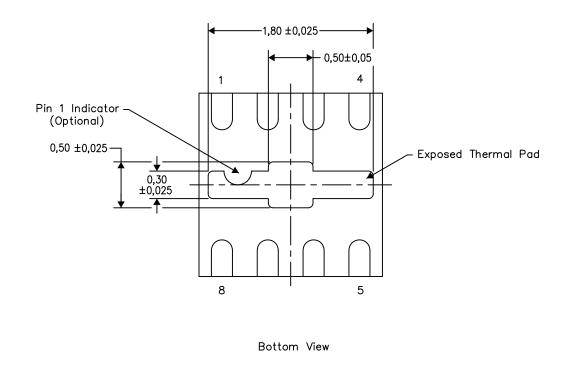
PLASTIC SMALL OUTLINE NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

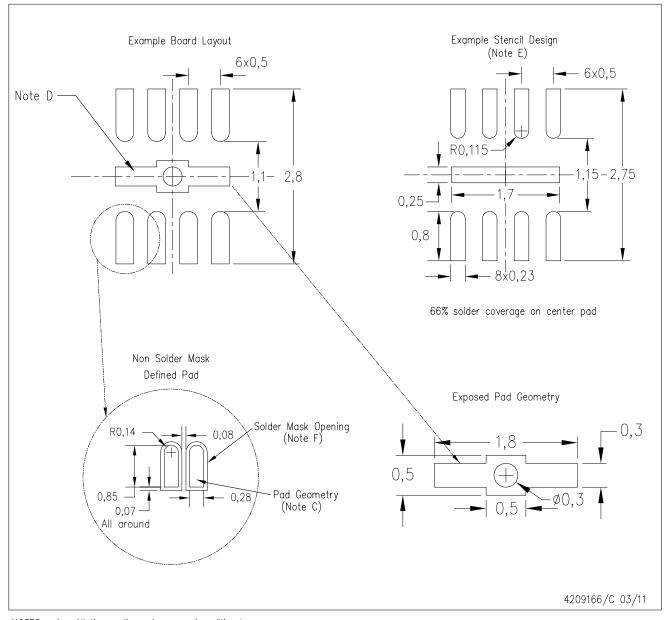
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NOTE: A. All linear dimensions are in millimeters



DRF (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



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